

SMD multilayer varistor array with Ni-barrier termination

CA05P4S14THSG B72714A8140S160

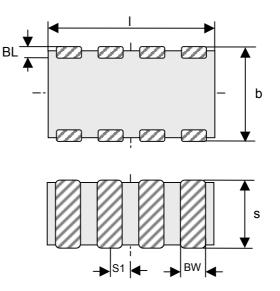
Designation system

- CA = <u>C</u>hip <u>a</u>rray
- = Dimensions of the device $\underline{05} \times 08$ (length x width in 1/100 inch)
- P = Design (**p**arallel internal structure)
- 4 = Number of elements
- S = <u>S</u>pecial tolerance of the varistor voltage
- 14 = Maximum operating voltage
- T = <u>T</u>hree layer terminations
- HS = Designed for protection of <u>h</u>igh <u>speed</u> datalines (low capacitance)
- G = Taped version (cardboard tape, 7" reel, 4000 pieces/reel)

Figure

 $I = 2.0 \pm 0.2$ b = 1.25 ± 0.2 s = 0.9 max. BW = 0.3 ± 0.1 BL = 0.2 +0.2/ -0.1 S1 = 0.25 ± 0.1

(all dimensions in mm)



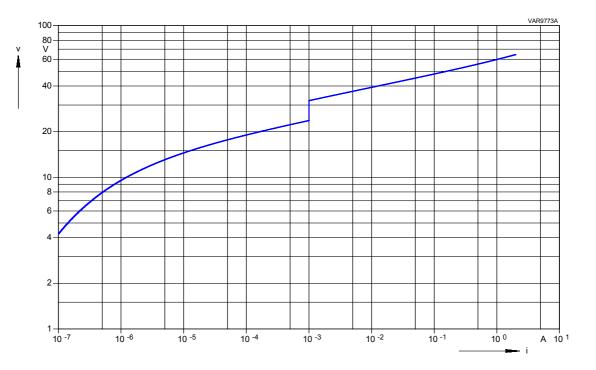
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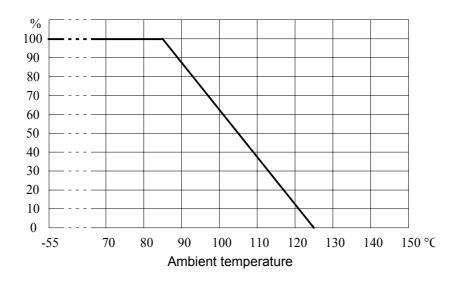
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V-I-characteristic



Max. current, energy and average power dissipation depending on ambient temperature



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Electrical data

Maximum operating voltage RMS voltage DC voltage	V _{RMS} = 14 V V _{DC} = 16 V
Varistor voltage (@ 1 mA) Maximum clamping voltage (@ 1 A)	V _V = 24 up to 32 V V _C = 59 V
DC leakage current (@ 4.2 V, 25 °C) DC leakage current (@ 4.2 V, 85 °C) Surface leakage current (@ 18 V, 25 °C)	I _S < 0.01 μA (typ.) I _S < 0.05 μA (typ.) I _{SL} < 0.1 μA
Insulation resistance after reflow soldering (@ $4.2 V, 25 °C$)	R _{IS} > 10 MΩ
Maximum capacitance (@ 1 MHz, 1 V, 25 °C) Typical capacitance (@ 1 MHz, 1 V, 25 °C)	C _{max} = 15 pF C _{typ} = 10 pF
Maximum energy absorption (ESD) (@ ESD according to IEC 61000-4-2, 15 kV air discharge)	W _{max} = 30 mJ
Response time	< 0.5 ns
Operating temperature Storage temperature (mounted parts)	–40 … +85 °C –40 … +125 °C
Termination material	Ag/Ni/Sn

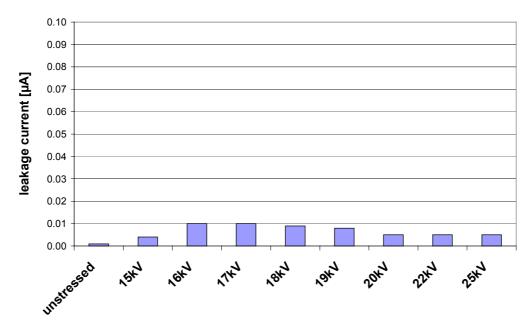
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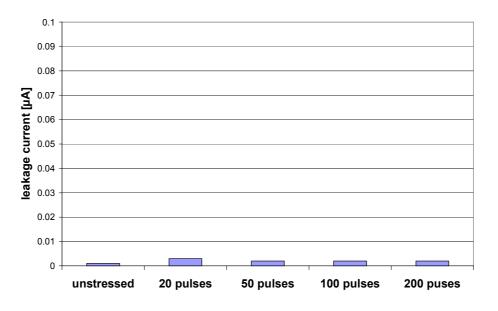
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Stability to multiple ESD discharges



Typical leakage current @ 4.2 V, 25 °C @ multiple ESD discharges (10 pulses of each polarity, contact discharge according to IEC 61000-4-2, voltage up to 25 kV, application on same parts).



Typical leakage current @ 4.2 V, 25 °C @ multiple ESD discharges (polarity +, 15 kV contact discharge according to IEC 61000-4-2).

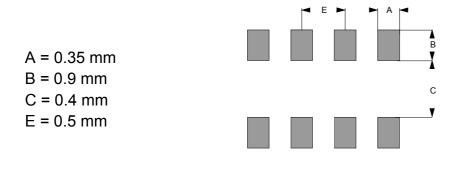


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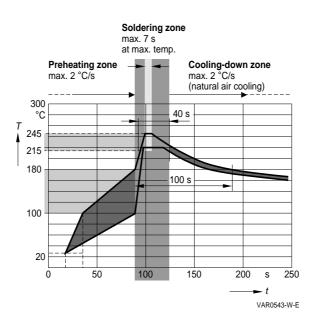
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Recommended geometry of solder pads



Recommended soldering temperature profile



This component is suited for reflow soldering. Maximum reflow cycles: 3 x

As far as possible, the components shall be employed within 12 months. They should be left in their original packings to avoid soldering problems due to oxidized terminals. Storage temperature: -25 to 45 °C

Relative humidity: < 75% annual average, < 95% on maximum 30 days in a year.

The usage of mild non-activated fluxes for soldering is recommended, as well as proper cleaning of the PCB.

The components are suited for Pb-free soldering.

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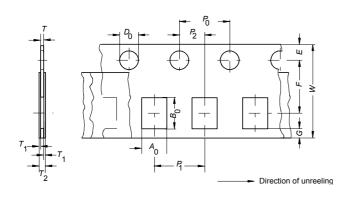
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Taping according to IEC 60286-3

Tape material: cardboard



Dimensions and tolerances:

Definition	Symbol	Dimension	Tolerance
		[mm]	[mm]
Compartment width	A ₀	1.6	± 0.2
Compartment length	B ₀	2.4	± 0.2
Sprocket hole diameter	D ₀	1.5	+0.1/ -0
Sprocket hole pitch	P ₀	4.0	± 0.1 ¹⁾
Distance center hole to center compartment	P ₂	2.0	± 0.05
Pitch of the component compartments	P ₁	4.0	± 0.1
Tape width	W	8.0	± 0.3
Distance edge to center of hole	E	1.75	± 0.1
Distance center hole to center compartment	F	3.5	± 0.05
Distance compartment to edge	G	0.75	min.
Overall thickness	T ₂	1.12	max.
Thickness tape	Т	0.95	± 0.05

 $^{1)} \le \pm 0.2$ mm over any 10 pitches Package: 8 mm tape:



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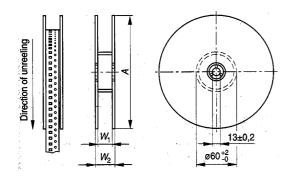
Packing

Each reel in airtight plastic bag with desiccant bag.

Reel material: plastic

Packing unit: 4000 pcs./reel

Reel dimensions:



Definition	Symbol	Dimension	Tolerance
		[mm]	[mm]
Reel diameter	А	180	+0 / _3
Reel width (inside)	W ₁	8.4	+1.5 /0
Reel width (outside)	W ₂	14.4	max.

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